JOILE TOLD										
FORM P	PTO-1449 JAN 2 8	DSI 302 APPLICATION NUMBER 10/815,994 N/8 01				ER 16,179				
	INFORMATION DISCLE	APPLICANTS Chung J. Lee et al.								
			FILING DATE March 31, 2004							
		U.S. PAT	ENT DOCUMENTS							
EXAMI		DATE	NAME	NAME CLASS SUB CLASS				IL. DATE APPROP.		
14	3,268,599	08/23/1966	Chow		1	141	1			
	3,274,267	09/20/1966	Chow			129	<u>' </u>			
	3,280,202	10/18/1966	Gilch	5	70	141	1			
	3,288,728	11/29/1966	Gorham		1	Se				
	3,332,891	07/25/1967	Chow et al.			39	I			
	3,342,754	09/19/1967	Gorham et al.		39		7			
	3,349,045	10/24/1967	Gilch	5	528 397		7			
	3,379,803	04/23/1968	Tittmann et al.	0	64	8				
V	3,503,903	03/31/1970	Shaw et al.	S	28	396				
		FOREIGN P.	ATENT DOCUMEN	TS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS		UB .ASS	TRANS YES	SLATION NO		
10	EP 0 349 032 A2	01/03/1990	EPO							
	EP 0 523 479 A2	01/20/1993	EPO							
\bigvee	EP 0 856 503 A1	08/05/1998	EPO							
		OTHE	R DOCUMENTS							
	Chow et al., <i>Poly</i> 9, pp. 2325-2332,		ro-p-xylylene), <u>Journal of</u>	Applied	l Polyr	ner Sci	ence, Vo	ol. 13, No.		
	Chow et al., The Synthesis of 1,1,2,2,9,9,10,10-octafluorou2, 2Paracyclophane, Journal of Organic Chemistry, Vol. 35, No. 1, pp. 20-22, 1970.									
	Iwamoto et al., Crystal Structure of Poly-p-xylylene. I. The a Form, Jour. Polymer. Sci. Polymer. Phys. Ed., Vol. 11, pp. 2403-2411, 1973.									
EXAMI	EXAMINER DATE CONSIDERED 1126/5									

FORM PTO-	1449	DOCKET NUMBER DSI 302		APPLICATION NUMBER 10/815,994 10/816,179				
	FORMATION DISCLO ATION IN AN APPLI	APPLICANTS Chung J. Lee et al.						
			FILING DATE March 31, 2004		GROUP ART UNIT			
		U.S. PAT	ENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLAS		ЛВ ASS	FIL DATE IF APPROP.	
17/2	3,509,075	04/28/1970	Niegish et al.	52	8 39	%		
(0)	3,626,032	12/07/1971	Norris	52	67			
	3,694,495	09/26/1972	Norris	Soc	2 40	16		
	3,940,530	02/24/1976	Loeb et al.	42	8 2	00		
	4,117,308	09/26/1978	Boggs et al.	39	2 30	20		
	4,518,623	05/21/1985	Riley	42	7-8	3		
	4,823,711	04/25/1989	Kroneberger et al.	Щ	0 2	36		
	4,996,010	02/26/1991	Modrek	Ula	44	01		
V	5,142,023	08/25/1992	Gruber et al.	52	183	54		
		FOREIGN PA	ATENT DOCUMENT	rs				
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TR. YES	ANSLATION NO	
10	GB 650 947	03/07/1951	Great Britain					
' (GB 673 651	06/11/1952	Great Britain					
	WO 97/15699	05/01/1997	WIPO					
		OTHE	R DOCUMENTS					
	Iwamoto et al., Cr Molecular Oriente Vol. 13, pp. 1925	ation as a Function	g Polymerization of Poly- of Temperature, <u>Journal</u> o	p-xylene. I of Polymei	II. Cryst	al Struc Polyme	ture and er. Phys. Ed.,	
Lee, Transport Polymerization of Gaseous Intermediates and Polymer Crystal Growth, J. Macromol. Sci. Rev. Macromol. Chem., C16(1), p. 79-127, 1977-78.							Macromol.	
	Sharma et al., Opti Science, Vol. 36,	timizing Poly(chlor No. 7, pp. 1555-15	o-p-Xylelene) or Parylene 65, Sept. 20, 1988.	C Synthes	is, <u>Journ</u>	al of Ap	plied	
EXAMINER	EXAMINER DATE CONSIDERED (1/24)							
-t	- V /	1			1			

FORM PTO	-1449	DOCKET NUMBER		APPLICATION NUMBER 10/815,99410/816,170					
	IFORMATION DISCL TATION IN AN APPLI	APPLICANTS Chung J. Lee et al.							
			FILING DATE March 31, 2004	GROUP ART UNIT					
		U.S. PAT	ENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CL			FIL. DATE IF APPROP.		
Wo	5,217,559	06/08/1993	Moslehi et al.	13	2 34	5.35			
10	5,268,202	12/07/1993	You et al.	42		5.6			
	5,320,518	06/14/1994	Stilger et al.	43	1 7				
	5,475,080	12/12/1995	Gruber et al.	So	18 3	54			
	5,482,009	01/09/1996	Kobayashi et al.	12	2 36	7.1			
	5,538,758	07/23/1996	Beach et al.	42	72	35.6			
	5,572,884	11/12/1996	Christensen et al.	6	247	6			
·	5,639,512	06/17/1997	Nonaka et al.	42	7/6	3,2			
1	5,648,006	07/15/1997	Min et al.	al	9 4	14.			
		FOREIGN PA	ATENT DOCUMEN	rs					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRAN YES	SLATION NO		
1/2	WO 97/15951	05/01/1997	WIPO						
49	WO 97/42356	11/13/1997	WIPO						
1/	WO 99/21705	05/06/1999	WIPO						
V		OTHE	R DOCUMENTS						
A	Macromolecular !	Science, Part C - Pe	Polyquinoxalines: Tg-Str olymer Reviews (formerly r Chemistry and Physics)	Journal o	of Macror	nolecular	l of Science,		
	Lang, Vapor Deposition of Very low k Polymer Films, Poly (Naphthalene), Poly (Fluorinated Naphthalene), Materials Research Society Symposium Proceedings, Vol. 381, pp. 45-50, April 17, 1995.								
Wary et al., Polymer Developed to be Interlayer Dielectric, Semi-Conductor International, pp. 211-216, June 1996.									
EXAMINE	hot &	ii	DATE CONSIDERED	upra	2/5				
1	(1/)			T	V				

FORM	1 PTO	-1449	DOCKET NUMBER		APPLICATION NUMBER 10/815,994 10/816,179				
		IFORMATION DISCL FATION IN AN APPL	APPLICANTS Chung J. Lee et al.						
				FILING DATE March 31, 2004		GROUP ART UNIT			
			U.S. PAT	ENT DOCUMENTS					
	MINER ITIAL	DOCUMENT NUMBER	DATE	NAME	CL		LASS	FIL DATE IF APPROP.	
Va		5,879,808	03/09/1999	Wary et al.	42	8 41			
70		5,945,170	08/31/1999	Kozak et al.	42	7 4	37		
		5,958,510	09/28/1999	Sivaramakrisham	Ŭρ	72	35.6		
		6,051,321	04/18/2000	Lee et al.	42	8 4	47		
		6,130,171	10/10/2000	Gomi	UZ	87	8		
		6,140,456	10/31/2000	Foggiator	52	8 19	6		
		6,144,802	11/07/2000	Kim	39	24	79		
		6,265,320	07/24/2001	Shi et al.	4	38 7	Z Z		
	/	6,302,874	10/16/2001	Zhang	60	×4 €	74		
	-		FOREIGN P.	ATENT DOCUMENT	rs	-			
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	YES	RANSLATION NO	
1	D	WO 99/21706	05/06/1999	WIPO					
		WO 99/21924	05/06/1999	WIPO					
	/	WO 99/22043	05/06/1999	WIPO					
			OTHE	R DOCUMENTS					
1/1	1	Wunderlick, Crys 246-247, 1996.	stal Nucleation, Gre	owth, Annealing, Macromo	olecular P	hysics, V	ol. 1-2,	pp. 242-243,	
V	Greiner, Poly(1,4-xylylene)s: Polymer Films by Chemical Vapour Deposition, Trends in Polymer Science, Vol. 5, No. 1, pp. 12-16, 1997.								
ş	J			e _R Material Candidate for <u>iety Symposium Proceedi</u>				ect	
EXAMINER DATE CONSIDERED 1/26/5									
		11//			1	-t			

FORM PTO-1449				DOCKET NUMBER DSI 302		APPLICATION NUMBER 10/815,994 10/816)79					
		FORMATION DISCLO ATION IN AN APPLI		APPLICANTS Chung J. Lee et al.							
				FILING DATE March 31, 2004 GROUP ART UNIT 2827 FILING DATE GROUP ART UNIT							
			U.S. PAT	ENT DOCUMENTS							
	MINER TIAL	DOCUMENT NUMBER	DATE	NAME	CL		SUB CLASS	FIL. DATE IF APPROP.			
//6	M	6,703,462	03/09/2004	Lee	5	26/2	42				
		6,797,343	09/28/2004	Lee	42	18 1],]	_			
		2002/0050659	05/02/2002	Toreki et al.	261	1 4	le				
		2002/0120083	08/29/2002	Lee	52	62	42				
		2003/0051662	03/20/2003	Lee	10	8 /	Q				
		2003/0072947	04/17/2003	Lee	42	8 4	21				
		2003/0143341	07/31/2003	Lee	14)	18/1					
		2003-0188683	10/9/2003	Lee	10	8 8	V-1				
		2003-0195312	10/16/2003	Lee	5	86	142				
			FOREIGN P	ATENT DOCUMENT	ΓS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	YES	RANSLATION NO			
		<u> </u>									
			OTHE	R DOCUMENTS		•	*********				
1/9	le			Conditions on the Proper							
1				Annealing on the Thermomposium Proceedings, Vo							
		Yang et al., High L 385-390, 1998.	Yang et al., High Deposition Rate Parylene Films, Journal of Crystal Growth, Vol. 183, No. 3, pp. 385-390, 1998.								
\	Mathur et al., Vapor Deposition of Parylene-F Using Hydrogen as Carrier Gas, Journal of Materials Research, Vol. 14, No. 1, pp. 246-250, 1999.										
EXAM	IINER	1/1/) ie	DATE CONSIDERED	UT.	26					

FORM PTO-	1449	DOCKET NUMBER DSI 302		APPLICATION NUMBER 10/815,99410/816, 179					
	FORMATION DISCLO ATION IN AN APPLI		APPLICANTS Chung J. Lee et al.						
			FILING DATE GROUP ART UNI March 31, 2004 GROUP ART UNI 2827				TUNI	r)	
		U.S. PAT	ENT DOCUMENT	CS					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME		CLASS	CL	UB ASS		L. DATE APPROP.
18	2003-0198578	10/23/2003	Lee		428	13	8	·	
Ho	2003-0196680	10/23/2003	Lee		134	l.	[
,						-			
						+	\dashv		
				· · · · · ·		-			***************************************
		FOREIGN P.	ATENT DOCUME	NTS			<u>-</u>		
	DOCUMENT NUMBER	DATE	COUNTRY	CL	ASS	SUB CLASS	T YES		ATION NO
		OTHE	R DOCUMENTS						
VS			itions in Fluorinated an edings, Vol. 565, pp. 29			ited Pa	rylene	s, <u>M</u> a	terial_
*	Brun, 100nm: The	Undiscovered Co	untry, Semiconductor I	nternatio	onal, p.	79, Fel	bruary	2000	
			s and Energy Partition Vol. 113, No. 17, pp. 7				ssociat	ion o	f Halon
	Rashed, Properties and Characteristics of Silicon Carbide, website publication (www.poco.com), POCO Graphite Inc., 2002.								
EXAMINER	AJL.	N	DATE CONSIDERED	1	126	, 1	S		
	KAD VA				1	V			<u></u> J

	Barrer S.	,	1 7 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1	·					
FORM PTO-	1449		DOCKET NUMBER APPLICATION NUMBER 10/816,179						
	FORMATION DISCI ATION IN AN APPL		APPLICANTS Chung J. Lee et al.						
			FILING DATE GROUP ART UNIT March 31, 2004 1763						
		U.S. PAT	ENT DOCUMENTS	si-C-					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CL			FIL DATE IF APPROP.		
1/2	3,503,903	3/31/70	Shaw et al.	S	28 39	16			
	6,086,952	7/11/00	Lang et al.	42	725	1.29			
	6,130,171	10/10/00	Gomi		7	8]			
	6,265,320	7/24/01	Shi et al.		7)	グ	•		
	6,455,443	9/24/02	Eckert et al.	43	87	8)			
V	6,495,208	12/17/02	Desu et al.	42	7/25	5.3	,		
		FOREIGN P	ATENT DOCUMEN	TS					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRAN YES	ISLATION NO		
	<u> </u>								
				<u> </u>					
		OTHE	R DOCUMENTS						
	Parylene Copolyn	ners, Taylor et al., <u>I</u>	ow Dielectric Constant M	laterials II	<u>I</u> , pp. 197	-205, 199	7.		
1	Finer Copper Wir 1999.	es Make for Faster	Integrated Circuits, Preus	s, <u>Researc</u>	h News, 1	pp. 1-3, A	pril 5,		
			ahigh Molecular Weight P of Materials Research, V						
	A Novel Oxazole I Semiconductor Fal	Based Low k Dielecotech, 12th Edition,	tric Addresses Copper Da pp. 231-235, July 2000.	mascene N	veeds, Scl	hmid et al.	,		
	The Effect of Water Desorption and Organosilane Coupling Agents on the Adhesion of Poly(p-xylylene) Films to a Silicon Wafer Surface, Lightfoot et a I., Journal of Materials Science: Materials in Electronics, Vol. 12, pp. 581-586, 2001.								
	Current Technical Trends: Dual Damascene & Low-k Dielectrics, Healey on behalf of Threshold Systems, pp. 1-6, © 2002.								
EXAMINER	1//		DATE CONSIDERED	1/2	1	/			